

PROCEEDINGS OF SPIE

29th European Mask and Lithography Conference

Uwe F.W. Behringer
Wilhelm Maurer
Editors

25–27 June 2013
Dresden, Germany

Organized by
VDE/VDI GMM—The Society for Microelectronics,
Micro- and Precision Engineering (Germany)

Published by
SPIE

Volume 8886

Proceedings of SPIE 0277-786X, V. 8886

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

29th European Mask and Lithography Conference, edited by Uwe F.W. Behringer,
Wilhelm Maurer, Proc. of SPIE Vol. 8886, 888601 · © 2013 SPIE
CCC code: 0277-786X/13/\$18 · doi: 10.1117/12.2048544

Proc. of SPIE Vol. 8886 888601-1

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Author(s), "Title of Paper," in *29th European Mask and Lithography Conference*, edited by Uwe F.W. Behringer, Wilhelm Maurer, Proceedings of SPIE Vol. 8886 (SPIE, Bellingham, WA, 2013) Article CID Number.

ISSN: 0277-786X

ISBN: 9780819497550

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445

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Foreword

On behalf of VDE/VDI-GMM, the sponsors, and the organizing committee, we welcome you to the proceedings volume from the 29th European Mask and Lithography Conference, EMLC2013, which was held at the Hilton Hotel in Dresden, Germany.

Each year this conference brings together scientists, researchers, engineers, and technologists from research institutes and companies from around the world to present innovations at the forefront of mask lithography and mask technology. The two and a half day conference was dedicated to the science, technology, engineering, and application of mask and lithography technologies and associated processes, giving an overview of the present status in mask and lithography technologies and the future strategy where mask producers and users have the opportunity of becoming acquainted with new developments and results. This year's sessions included: EUV Tooling & Further Lithography Options, Optical Lithography & APC, Mask Materials, E-beam Lithography, Metrology & Inspection, and Resolution Enhancement & DFM.

Dr. G. Teepe from GLOBALFOUNDRIES was the conference's welcome speaker. The first keynote speaker was Dr. H. Morimoto from Toppan Printing Company of Japan. His presentation was entitled "Photomask Technology Progress to meet with Electronics Product Requirements." Our second keynote speaker was Dr. H.J. Levinson from GLOBALFOUNDRIES. His presentation was entitled "The Lithographer's Dilemma: Shrinking without Breaking the Bank."

As a tradition we invited the Best Paper of PMJ 2013 and the Best Poster from Photomask Space 2012 to present their papers at the EMLC2013.

A Panel Session "EUVL – What else?" took place on Wednesday afternoon. The panelists were: H. Morimoto from Toppan; H.J. Levinson from GLOBALFOUNDRIES; F. Goodwin from SEMATECH; N. Hayashi, from DNP; J. Finders from ASML; and J.H. Peters from Carl Zeiss SMS. S. Wurm from SEMATECH acted as Session Chair and Moderator.

Parallel to the Conference Presentations, the Technical Exhibition took place on Tuesday afternoon (1:00 PM), and continued all of Wednesday, and concluded Thursday afternoon (1:00 PM). Some of the exhibitor companies were: Vistec E-Beam; Photronics; Entegris; Nuflare; PI; Pozzetta; Carl Zeiss; JEOL; S3Alliance; Sitem; ibss Group. EQUIcon informed us on their products and support.

We hope that you enjoyed the Technical Sessions of the EMLC2013 as well as the Technical Exhibition, but also allow yourself to visit Dresden!

Uwe F.W. Behringer

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The 29th European Mask and Lithography Conference, EMLC would like to express its sincere appreciation to all the sponsors and cooperating partners mentioned below for their support.



